

1N4148

Small Signal Switching Diode

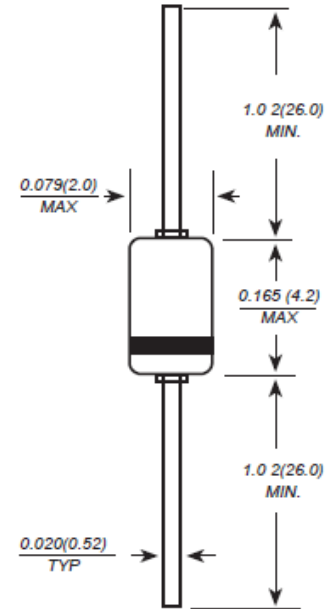
◆ Features

- » Silicon epitaxial planar diode
- » 500mw power dissipation
- » Soldering:
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension

◆ Mechanical Data

- » **Case:** DO-35 glass sealed envelope.
- » **Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026
- » **Polarity:** Color band denotes cathode end
- » **Weight:** 0.005 ounce, 0.14 grams
- » **Standard Package:** Ammopack

DO-35



Dimensions in inches and (millimeters)

Ratings at 25 C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

PARAMETER	SYMBOL	1N4148	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	100	VOLTS
Maximum RMS voltage	V _{RMS}	75	VOLTS
Maximum average forward rectified current 0.375" (9.5mm) lead length at T _A =25 C	I _(AV)	150	mAmps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	500	mAmps
Maximum instantaneous forward voltage at 10mA	V _F	1.0	Volts
Maximum DC reverse current T _A =25°C V _R =75V at rated DC blocking voltage T _A =100°C V _R =20V	I _R	5.0 50	mA
Maximum reverse recovery time (NOTE 1)	t _{rr}	4.0	ns
Typical junction capacitance (NOTE 2)	C _J	4.0	pF
Operating junction and storage temperature range	T _J , T _{STG}	-65 to +200	°C

NOTES:

1. Test condition: I_F=10mA, I_R=10mA, I_{rr}=1mA, V_R=6V, R_L=100W.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts

◆ Rating And Characteristic Curves

FIG. 1-ADMISSIBLE POWER DISSIPATION VERSUS AMBIENT TEMPERATURE

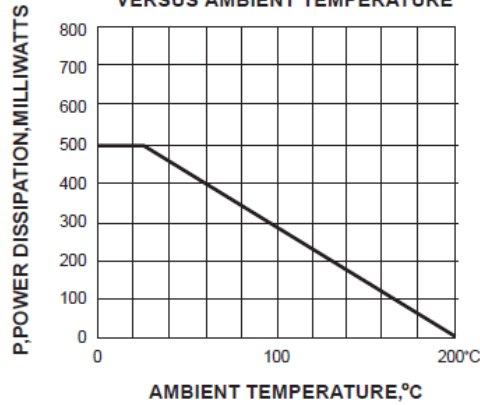


FIG. 2-REVERSE CURRENT VERSUS CONTINUOUS REVERSE VOLTAGE (TYPICAL VALUES)

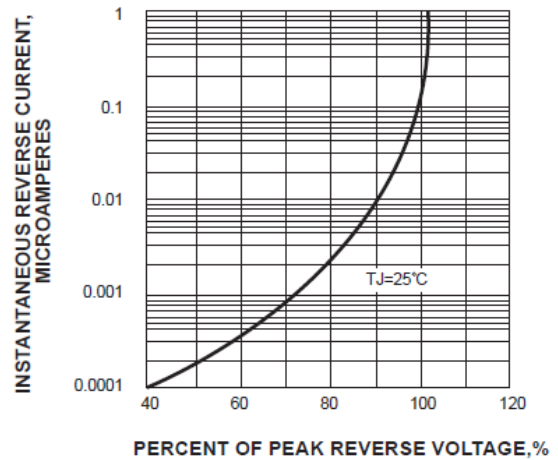


FIG. 3-FORWARD CHARACTERISTICS

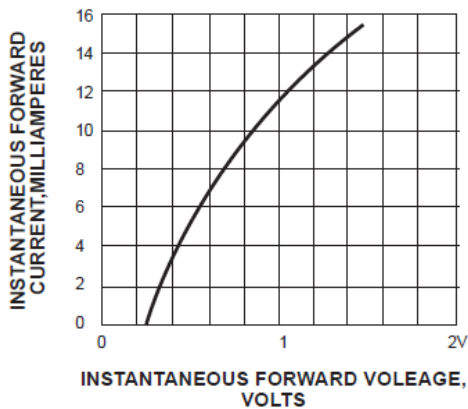


FIG. 4-RELATIVE CAPACTANCE VERSUS REVERSE VOLTAGE

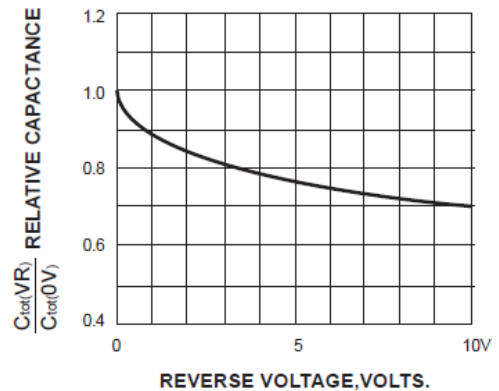


FIG. 5-ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

